Amplifier Transistor

PNP Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

| Rating | Symbol Value | | Unit | |
|---|-----------------------------------|----------------|-------------|--|
| Collector - Emitter Voltage | V _{CEO} | -60 | Vdc | |
| Collector - Base Voltage | V _{CBO} | -60 | Vdc | |
| Emitter - Base Voltage | V _{EBO} | -5.0 | Vdc | |
| Collector Current - Continuous | Ic | -600 | mAdc | |
| Total Device Dissipation @ T _A = 25°C Derate above 25°C | P _D | 625 5.0 | mW mW/°C | |
| Total Device Dissipation @ T _C = 25°C Derate above 25°C | P _D | 1.5 12 | W mW/°C | |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -55 to +150 | °C | |

THERMAL CHARACTERISTICS

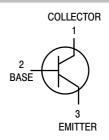
| Characteristic | Symbol | Max | Unit | |
|---|-----------------|------|------|--|
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 200 | °C/W | |
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 83.3 | °C/W | |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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P2N2 = Device Code 907A = Specific Device = Assembly Location Α

= Year WW = Work Week = Pb-Free Package (Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|--------------|--------------------|-----------------------|
| P2N2907A | TO-92 | 5000 Units / Bulk |
| P2N2907AG | TO-92 (Pb-Free) | 5000 Units / Bulk |
| P2N2907ARL1 | TO-92 | 2000 / Tape & Reel |
| P2N2907ARL1G | TO-92 (Pb-Free) | 2000 / Tape & Reel |
| P2N2907AZL1 | TO-92 | 2000 / Tape & Ammo |
| P2N2907AZL1G | TO-92 (Pb-Free) | 2000 / Tape & Ammo |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

| Characteristic | | | Min | Max | Unit |
|---|---|----------------------|-------------------------------|--------------------|------|
| OFF CHARACTERISTICS | | - | | - | |
| Collector – Emitter Breakdown Voltage (Note 1) (I _C = -10 mAdc, I _B = 0) | | | -60 | - | Vdc |
| Collector – Base Breakdown Voltage (I _C = –10 μAdc, I _E = 0) | | V _{(BR)CBO} | -60 | - | Vdc |
| Emitter – Base Breakdown Voltage $(I_E = -10 \mu Adc, I_C = 0)$ | | | -5.0 | _ | Vdc |
| Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc) | | I _{CEX} | - | -50 | nAdc |
| Collector Cutoff Current $(V_{CB} = -50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -50 \text{ Vdc}, I_E = 0, T_A = 150^{\circ}\text{C})$ | | I _{CBO} | - - | -0.01 -10 | μAdc |
| Emitter Cutoff Current (V _{EB} = -3.0 Vdc) | | I _{EBO} | - | -10 | nAdc |
| Collector Cutoff Current (V _{CE} = -10 V) | | I _{CEO} | - | -10 | nAdc |
| Base Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc) | | I _{BEX} | - | -50 | nAdc |
| ON CHARACTERISTICS | | | | | 1 |
| $\begin{array}{l} \text{DC Current Gain} \\ & (I_C = -0.1 \text{ mAdc, V}_{CE} = -10 \text{ Vdc}) \\ & (I_C = -1.0 \text{ mAdc, V}_{CE} = -10 \text{ Vdc}) \\ & (I_C = -10 \text{ mAdc, V}_{CE} = -10 \text{ Vdc}) \\ & (I_C = -150 \text{ mAdc, V}_{CE} = -10 \text{ Vdc}) \\ & (I_C = -500 \text{ mAdc, V}_{CE} = -10 \text{ Vdc}) \end{array} \text{ (Note 1)} \\ & (I_C = -500 \text{ mAdc, V}_{CE} = -10 \text{ Vdc}) \end{array}$ | | h _{FE} | 75 100 100 100 50 | - - 300 - | _ |
| Collector – Emitter Saturation Voltage (Note 1 $(I_C = -150 \text{ mAdc}, I_B = -15 \text{ mAdc})$ $(I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc})$ | | V _{CE(sat)} | - - | -0.4 -1.6 | Vdc |
| Base – Emitter Saturation Voltage (Note 1) (I _C = -150 mAdc, I _B = -15 mAdc) (I _C = -500 mAdc, I _B = -50 mAdc) | | | - - | -1.3 -2.6 | Vdc |
| SMALL-SIGNAL CHARACTERISTICS | | | | • | • |
| Current – Gain – Bandwidth Product (Notes 1 and 2) (I _C = –50 mAdc, V _{CE} = –20 Vdc, f = 100 MHz) | | | 200 | - | MHz |
| Output Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz) | | | - | 8.0 | pF |
| Input Capacitance (V _{EB} = -2.0 Vdc, I _C = 0, f = 1.0 MHz) | | | - | 30 | pF |
| SWITCHING CHARACTERISTICS | | | | • | |
| Turn-On Time | | t _{on} | - | 50 | ns |
| Delay Time | $(V_{CC} = -30 \text{ Vdc}, I_{C} = -150 \text{ mAdc},$ $I_{B1} = -15 \text{ mAdc})$ (Figures 1 and 5) | t _d | - | 10 | ns |
| Rise Time | i _{B1} = -10 m/do) (Figures Fand 9) | t _r | - | 40 | ns |
| Turn-Off Time | | t _{off} | - | 110 | ns |
| torage Time $ (V_{CC} = -6.0 \text{ Vdc, } I_{C} = -150 \text{ mAdc,} $ $ I_{B1} = I_{B2} = -15 \text{ mAdc) (Figure 2)} $ | | ts | - | 80 | ns |
| Fall Time | t _f | _ | 30 | ns | |

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%. 2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

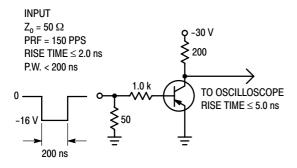


Figure 1. Delay and Rise Time Test Circuit

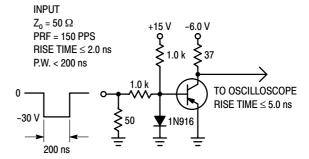


Figure 2. Storage and Fall Time Test Circuit

TYPICAL CHARACTERISTICS

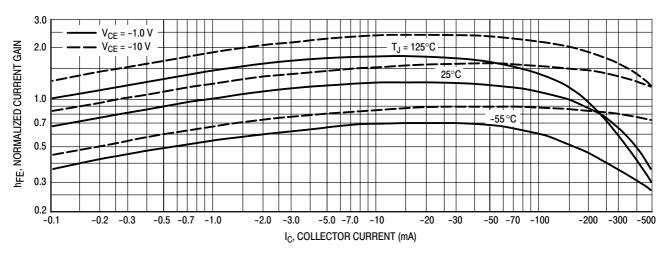


Figure 3. DC Current Gain

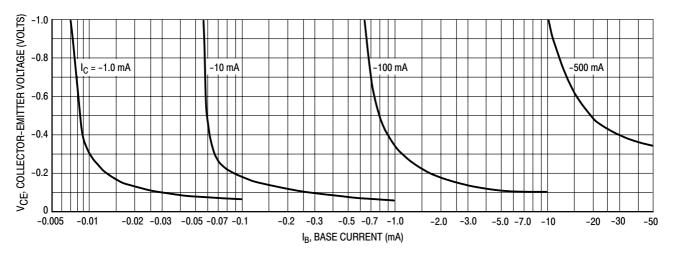


Figure 4. Collector Saturation Region

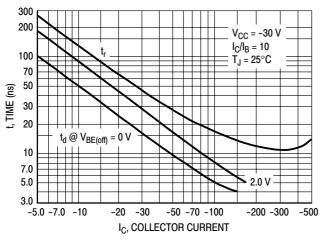


Figure 5. Turn-On Time

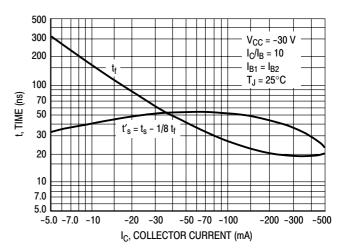


Figure 6. Turn-Off Time

TYPICAL SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

 V_{CE} = 10 Vdc, T_A = 25°C

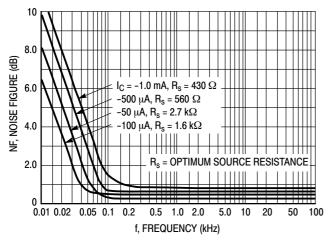


Figure 7. Frequency Effects

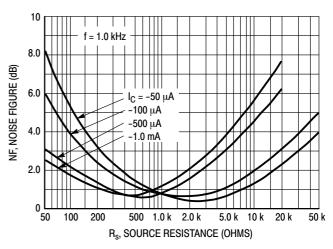


Figure 8. Source Resistance Effects

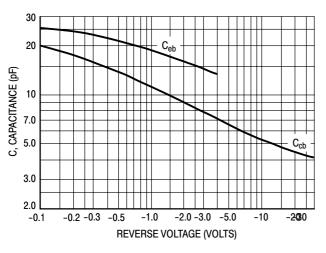


Figure 9. Capacitances

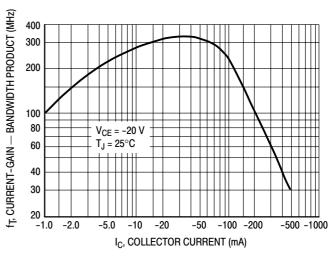


Figure 10. Current-Gain - Bandwidth Product

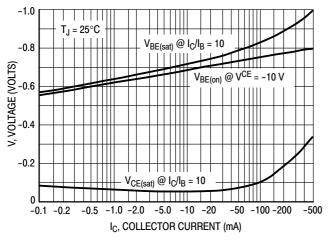


Figure 11. "On" Voltage

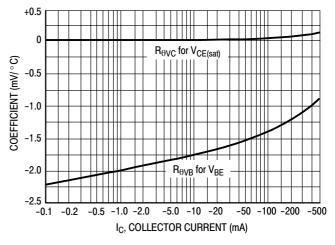
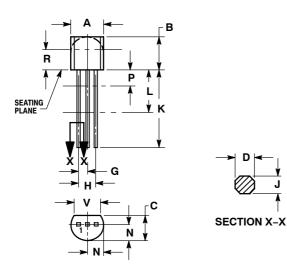


Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND
- BEYOND DIMENSION K MINIMUM.

| | INCHES | | MILLIN | IETERS |
|-----|--------|-------|--------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.175 | 0.205 | 4.45 | 5.20 |
| В | 0.170 | 0.210 | 4.32 | 5.33 |
| С | 0.125 | 0.165 | 3.18 | 4.19 |
| D | 0.016 | 0.021 | 0.407 | 0.533 |
| G | 0.045 | 0.055 | 1.15 | 1.39 |
| Н | 0.095 | 0.105 | 2.42 | 2.66 |
| J | 0.015 | 0.020 | 0.39 | 0.50 |
| K | 0.500 | | 12.70 | |
| L | 0.250 | | 6.35 | |
| N | 0.080 | 0.105 | 2.04 | 2.66 |
| P | | 0.100 | | 2.54 |
| R | 0.115 | | 2.93 | |
| V | 0.135 | | 3.43 | |

STYLE 17:

PIN 1. COLLECTOR

- 2. BASE
- **EMITTER**

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